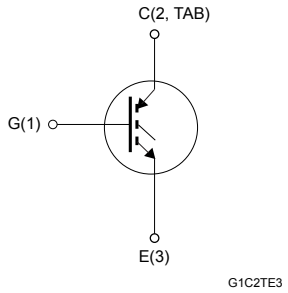
STGW25H120F2, STGWA25H120F2

Datasheet

Trench gate field-stop IGBT, H series 1200 V, 25 A high speed



Features

- Maximum junction temperature: T_J = 175 °C
- High speed switching series
- Minimized tail current
- $V_{CE(sat)}$ = 2.1 V (typ.) @ I_C = 25 A
- 5 µs minimum short circuit withstand time at T_J = 150 °C
- Safe paralleling
- Low thermal resistance

Applications

- Photovoltaic inverters
- Uninterruptible power supply
- Welding
- Power factor correction
- High frequency converters

Description

These devices are IGBTs developed using an advanced proprietary trench gate field-stop structure. The device is part of the H series IGBTs, which represent an optimum compromise between conduction and switching losses to maximize the efficiency of high-switching frequency converters. Furthermore, a slightly positive $V_{CE(sat)}$ temperature coefficient and very tight parameter distribution result in safer paralleling operation.

Product status links
STGW25H120F2
STGWA25H120F2

Product summary	
Order code	**STGW25H120F2**
Marking	G25H120F2
Package	TO-247
Packing	Tube
Order code	**STGWA25H120F2**
Marking	G25H120F2
Package	TO-247 long leads
Packing	Tube

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CES}	Collector-emitter voltage (V_{GE} = 0 V)	1200	V
I_C	Continuous collector current at T_C = 25 °C	50	A
	Continuous collector current at T_C = 100 °C	25	
I_{CP}(1)	Pulsed collector current	100	A
V_{GE}	Gate-emitter voltage	±20	V
P_{TOT}	Total power dissipation at T_C = 25 °C	375	W
T_J	Operating junction temperature range	- 55 to 175	°C
T_{STG}	Storage temperature range	- 55 to 150	°C

1. *Pulse width limited by maximum junction temperature.*

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	0.4	°C/W
R_{thJA}	Thermal resistance, junction-to-ambient	50	°C/W

2 Electrical characteristics

T_J = 25 °C unless otherwise specified.

Table 3. Static characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage	V_{GE} = 0 V, I_C = 2 mA	1200			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	V_{GE} = 15 V, I_C = 25 A		2.1	2.6	V
		V_{GE} = 15 V, I_C = 25 A, T_J = 125 °C		2.4		
		V_{GE} = 15 V, I_C = 25 A, T_J = 175 °C		2.5		
$V_{GE(th)}$	Gate threshold voltage	V_{CE} = V_{GE}, I_C = 1 mA	5	6	7	V
I_{CES}	Collector cut-off current	V_{GE} = 0 V, V_{CE} = 1200 V			25	µA
I_{GES}	Gate-emitter leakage current	V_{CE} = 0 V, V_{GE} = ±20 V			±250	nA

Table 4. Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	V_{CE} = 25 V, f = 1 MHz, V_{GE} = 0 V	-	2010	-	pF
C_{oes}	Output capacitance		-	146	-	pF
C_{res}	Reverse transfer capacitance		-	49	-	pF
Q_g	Total gate charge	V_{CC} = 960 V, I_C = 25 A, V_{GE} = 0 to 15 V (see Figure 22)	-	100	-	nC
Q_{ge}	Gate-emitter charge		-	11	-	nC
Q_{gc}	Gate-collector charge		-	52	-	nC

Table 5. Switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{CE} = 600 V, I_C = 25 A, R_G = 10 Ω, V_{GE} = 15 V (see Figure 21)		29	-	ns
t_r	Current rise time			12	-	ns
$(di/dt)_{on}$	Turn-on current slope			1774	-	A/µs
$t_{d(off)}$	Turn-off delay time			130	-	ns
t_f	Current fall time			106	-	ns
E_{on} (1)	Turn-on switching energy			0.6	-	mJ
E_{off} (2)	Turn-off switching energy			0.7	-	mJ
E_{ts}	Total switching energy			1.3	-	mJ
$t_{d(on)}$	Turn-on delay time	V_{CE} = 600 V, I_C = 25 A, R_G = 10 Ω, V_{GE} = 15 V, T_J = 175 °C (see Figure 21)		27.5	-	ns
t_r	Current rise time			13.5	-	ns
$(di/dt)_{on}$	Turn-on current slope			1522	-	A/µs
$t_{d(off)}$	Turn-off delay time			139	-	ns
t_f	Current fall time			200	-	ns
E_{on} (1)	Turn-on switching energy			1.05	-	mJ
E_{off} (2)	Turn-off switching energy			1.65	-	mJ
E_{ts}	Total switching energy			2.7	-	mJ
t_{sc}	Short-circuit withstand time	V_{CE} = 600 V, V_{GE} = 15 V, T_J = 150 °C,	5		-	µs

1. *Including the reverse recovery of the diode.*
2. *Including the tail of the collector current.*

2.1 Electrical characteristics (curves)

Figure 1. Power dissipation vs case temperature

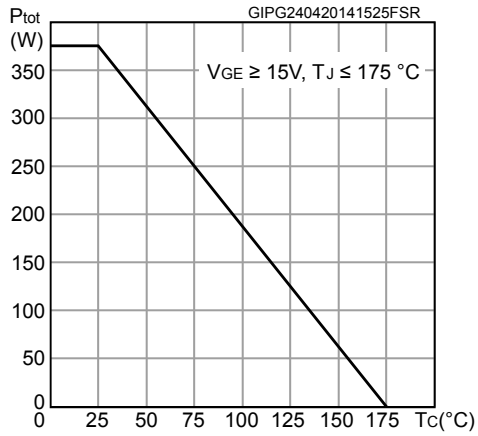


Figure 2. Collector current vs case temperature

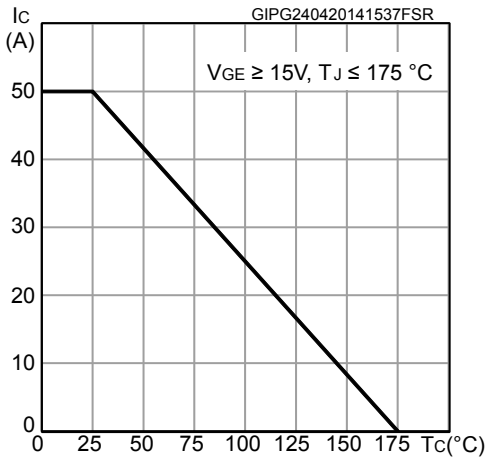


Figure 3. Output characteristics (T_J = 25 °C)

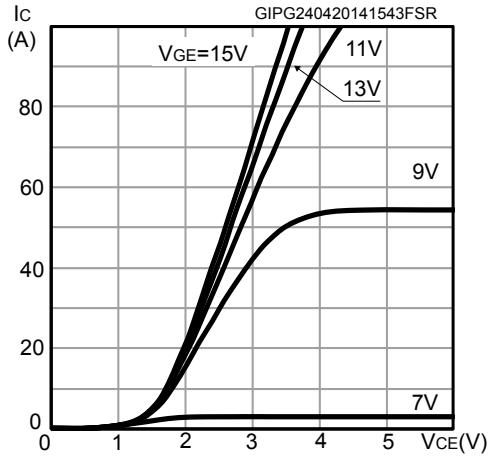


Figure 4. Output characteristics (T_J = 175 °C)

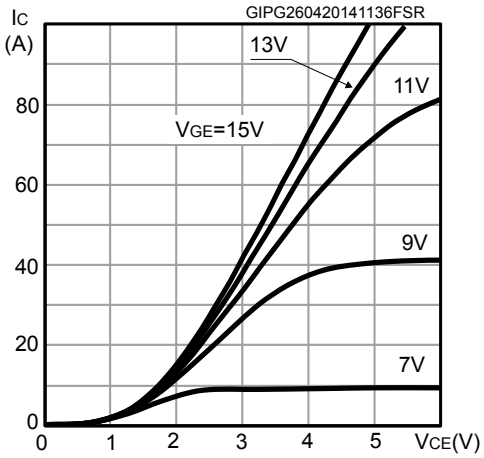


Figure 5. $V_{CE(sat)}$ vs junction temperature

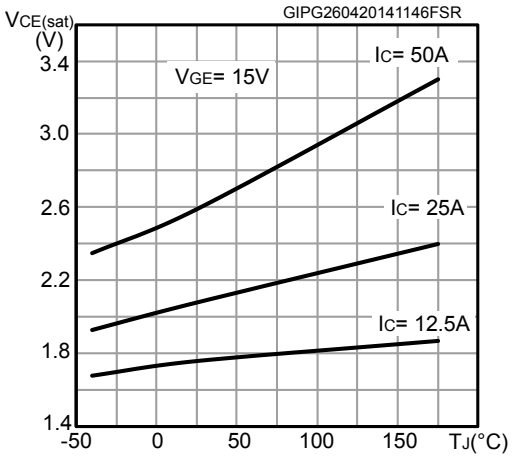


Figure 6. $V_{CE(sat)}$ vs collector current

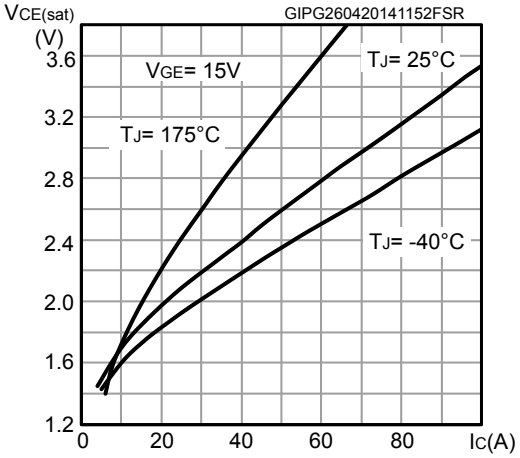


Figure 7. Collector current vs switching frequency

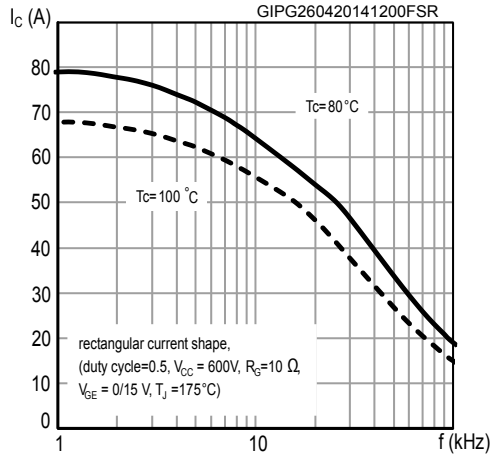


Figure 8. Safe operating area

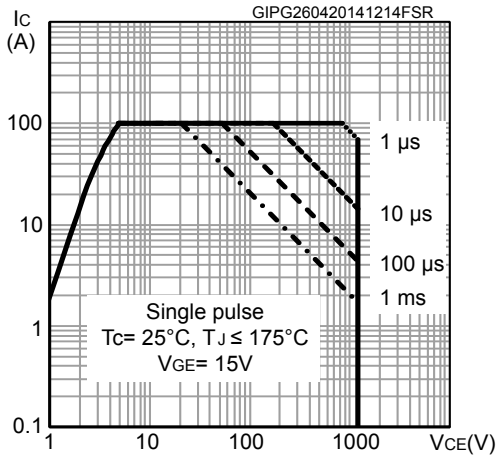


Figure 9. Transfer characteristics

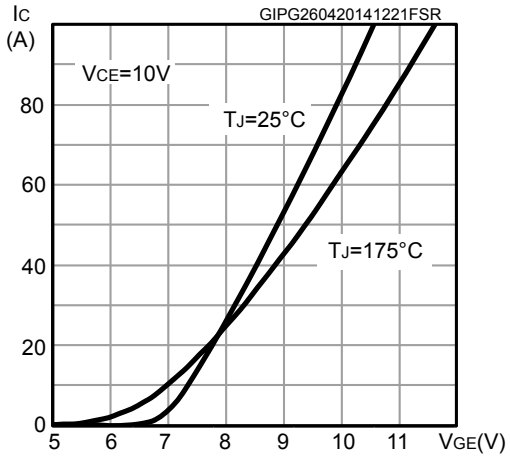


Figure 10. Diode V_F vs forward current

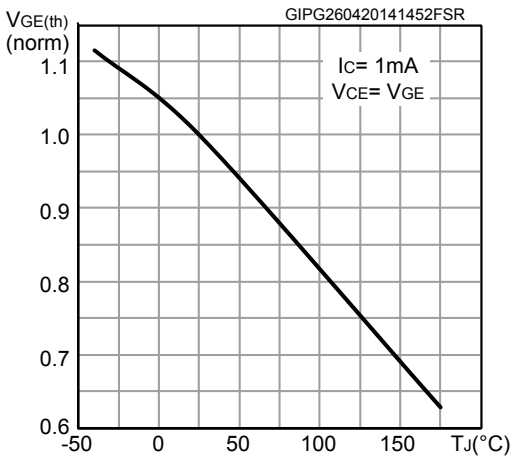


Figure 11. Normalized $V_{(BR)CES}$ vs junction temperature

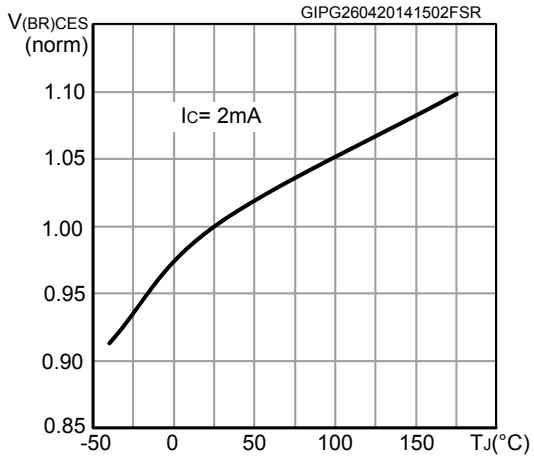


Figure 12. Capacitance variations

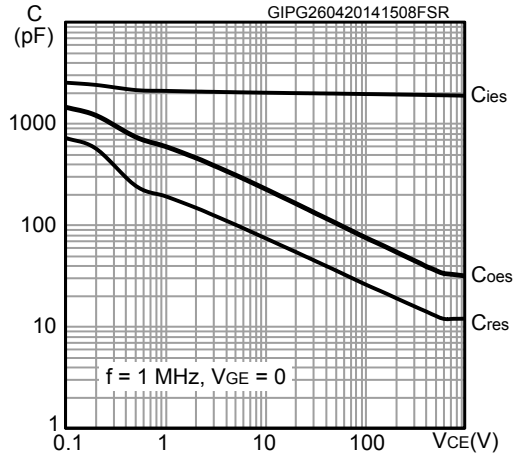


Figure 13. Gate charge vs gate-emitter voltage

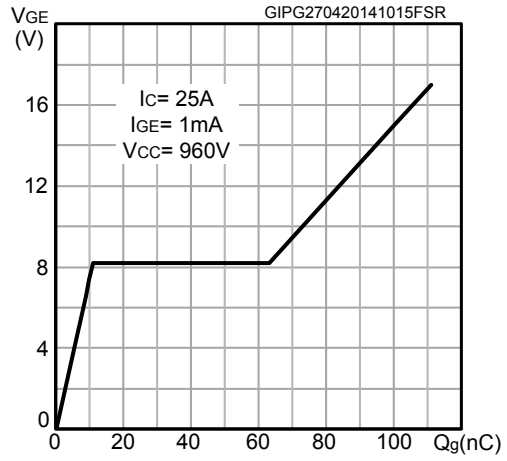


Figure 14. Switching energy vs collector current

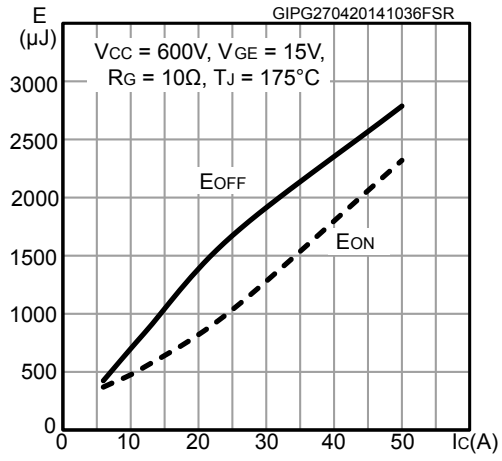


Figure 15. Switching energy vs gate resistance

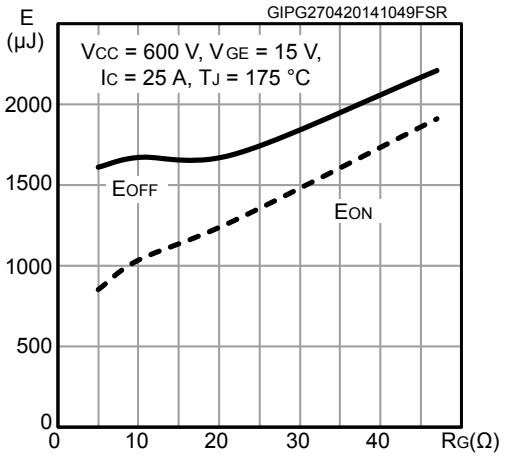


Figure 16. Switching energy vs junction temperature

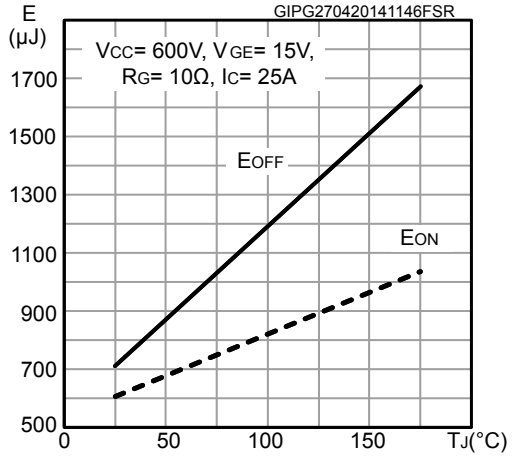


Figure 17. Switching energy vs collector-emitter voltage

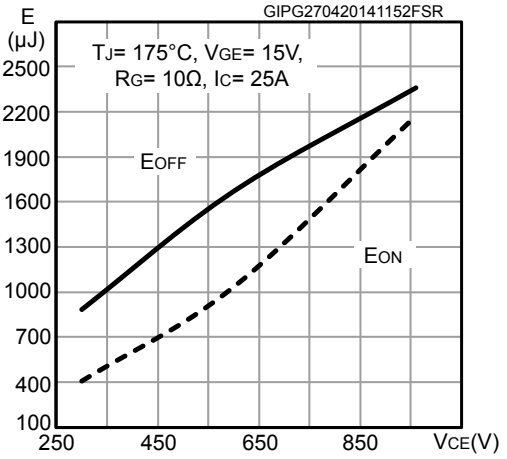


Figure 18. Switching times vs collector current

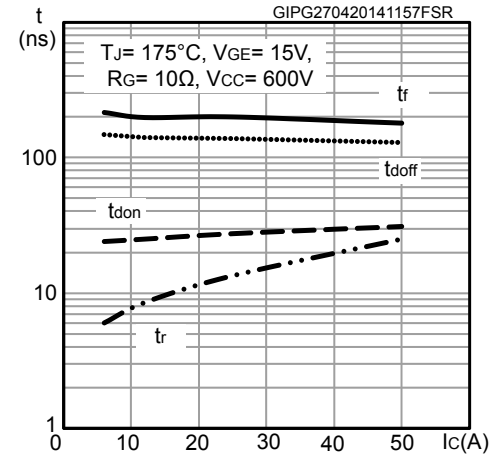


Figure 19. **Switching times vs gate resistance**

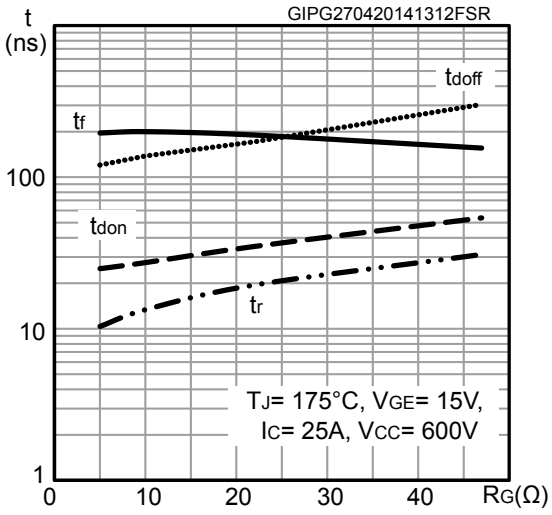
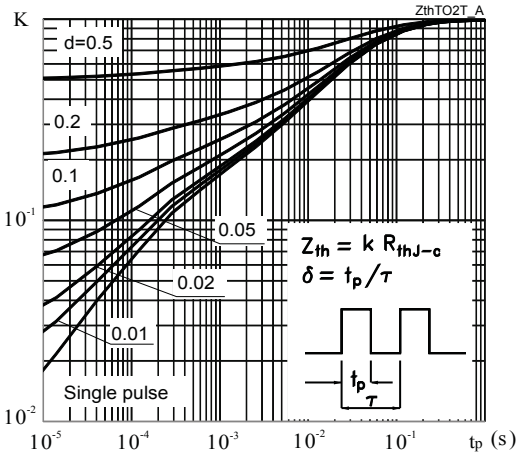


Figure 20. **Thermal impedance**



3 Test circuits

Figure 21. **Test circuit for inductive load switching**

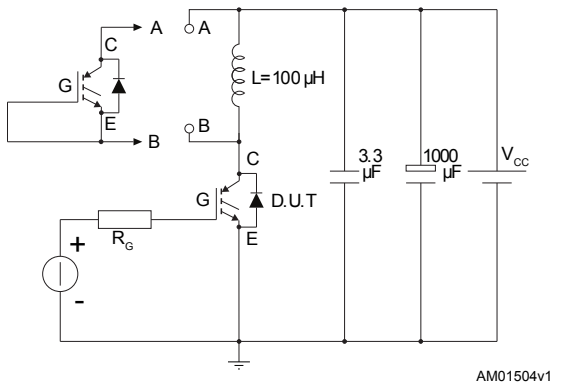


Figure 22. **Gate charge test circuit**

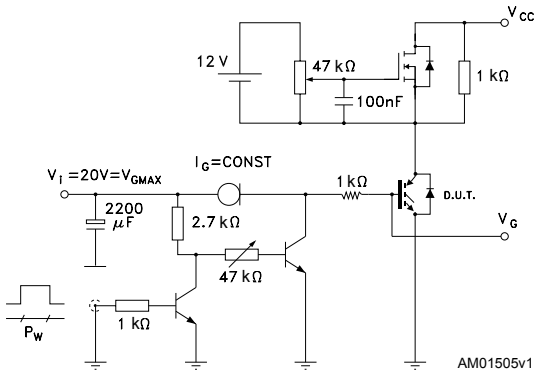
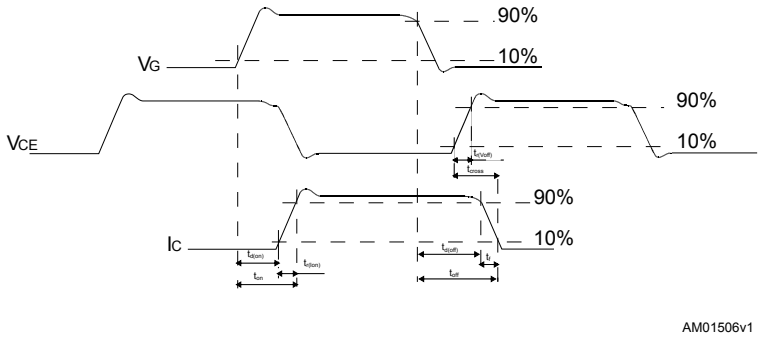


Figure 23. **Switching waveform**

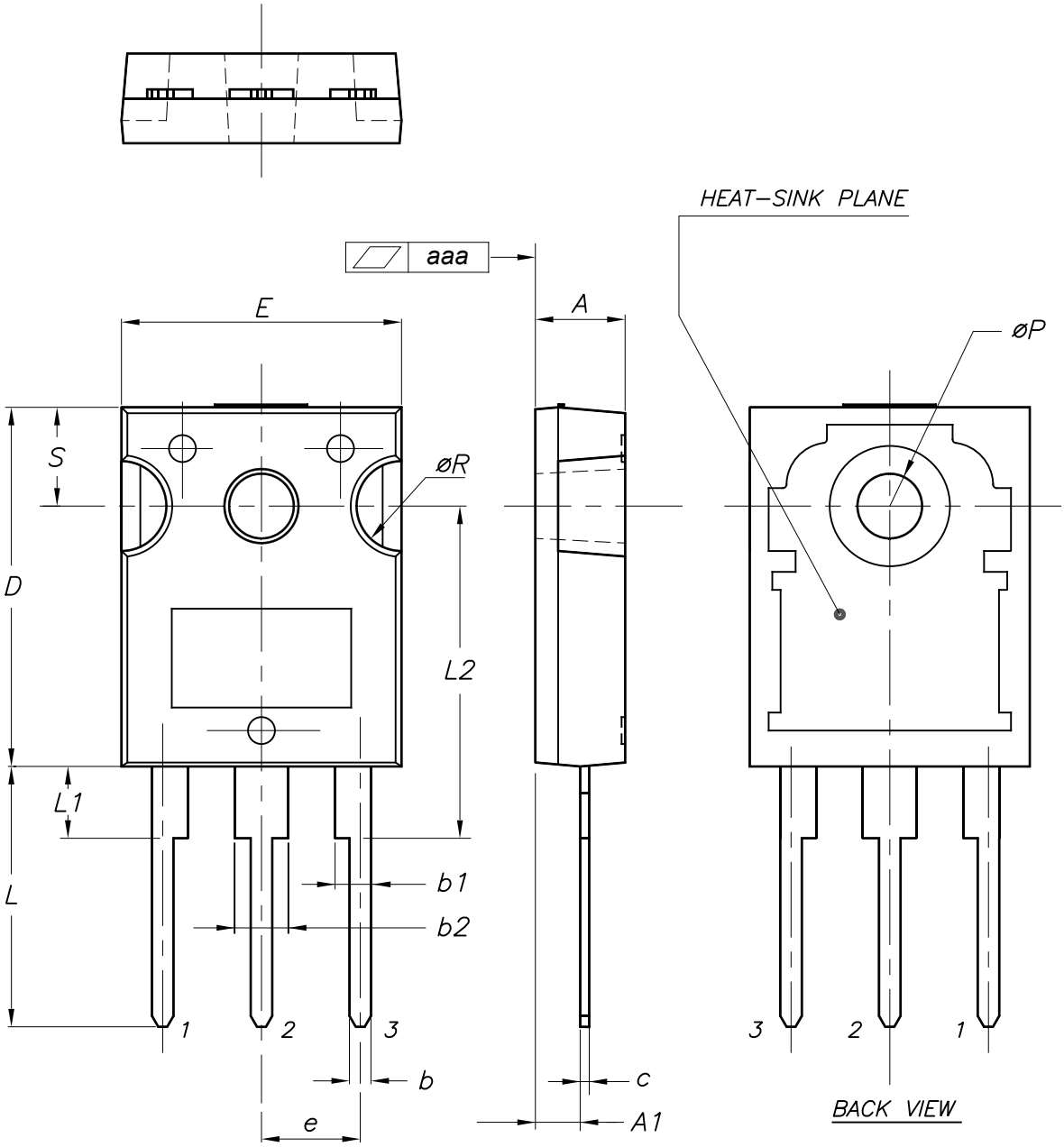


4 Package information

To meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 TO-247 package information

Figure 24. TO-247 package outline



0075325_10

Table 6. **TO-247 package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70
aaa		0.04	0.10

4.2 TO-247 long leads package information

Figure 25. **TO-247 long leads package outline**

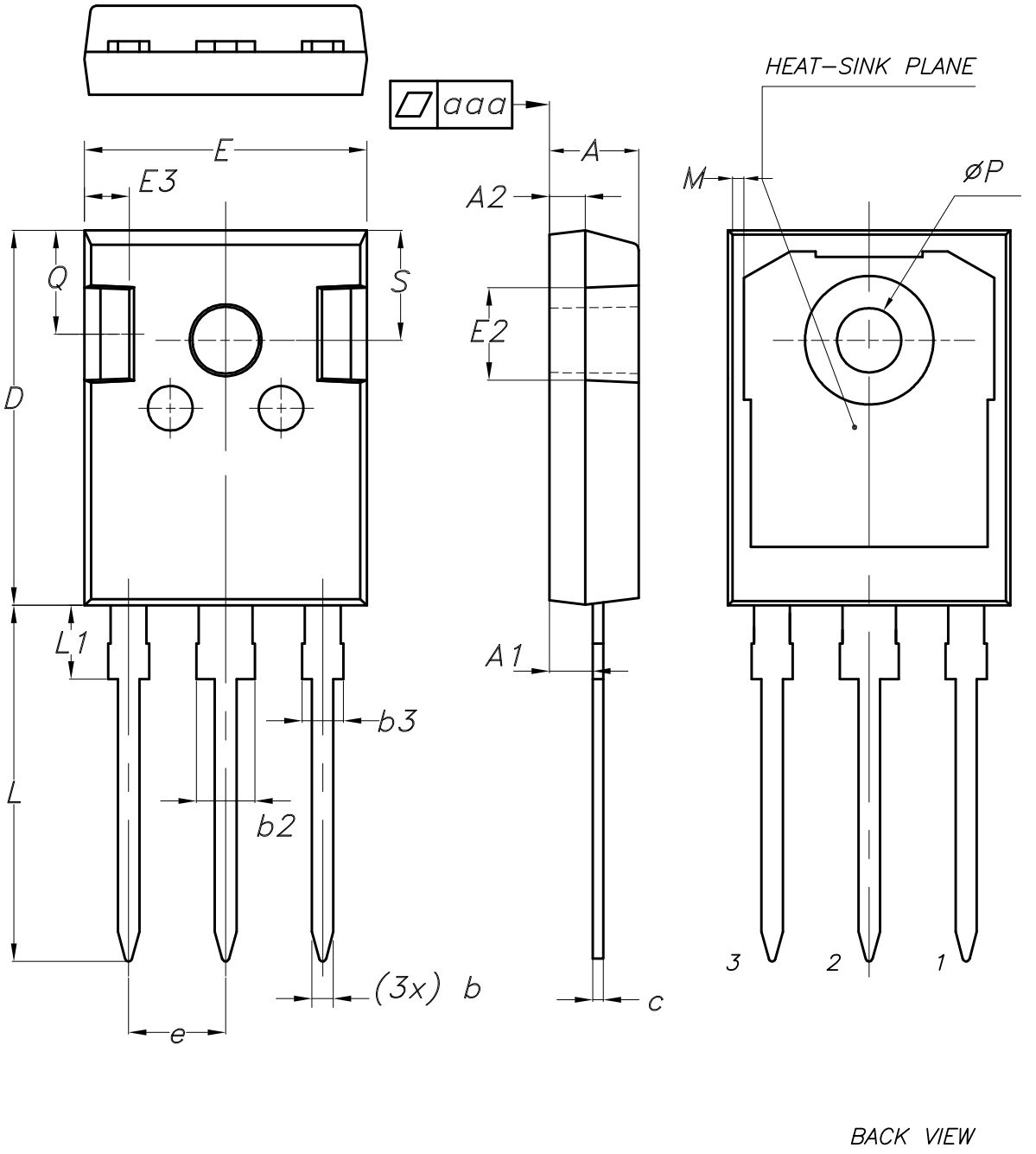


Table 7. **TO-247 long leads package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.90	5.00	5.10
A1	2.31	2.41	2.51
A2	1.90	2.00	2.10
b	1.16		1.26
b2			3.25
b3			2.25
c	0.59		0.66
D	20.90	21.00	21.10
E	15.70	15.80	15.90
E2	4.90	5.00	5.10
E3	2.40	2.50	2.60
e	5.34	5.44	5.54
L	19.80	19.92	20.10
L1			4.30
M	0.35		0.95
P	3.50	3.60	3.70
Q	5.60		6.00
S	6.05	6.15	6.25
aaa		0.04	0.10

Revision history

Table 8. **Document revision history**

Date	Revision	Changes
28-Feb-2014	1	Initial release.
31-Mar-2014	2	Document status changed from preliminary to production data. Updated *Table 4: Static characteristics* and *Table 6: Switching characteristics (inductive load)*. Added Section *2.1: Electrical characteristics (curves)*.
06-Mar-2015	3	Added *4.2: TO-247 long leads, package information*. Updated Features and *Figure 23.: Gate charge test circuit*. Minor text changes
23-Mar-2015	4	Removed figures with diode. Minor text changes.
11-Feb-2025	5	Updated Section 4.1: TO-247 package information, and Section 4.2: TO-247 long leads package information. Minor text changes.

Contents